



The attenuator is designed for RF power level adjustment. SYMAIR RF attenuators have compact dimensions, stable power handling and high reliability for long-term applications. Additionally, SYMAIR can offer low PIM models for variable PIM value requirements.

*\*XX refers to the optional attenuation values.*

### General Specifications

Product Type	RF Attenuator
Frequency Band	DC-6000 MHz
Power Handling	1 Watt
Connector Interface	N-male to N-female

### Electrical Specifications

Frequency Band	DC-6000 MHz						
Return Loss	≤-20.8 dB for DC-3000MHz ≤-19.1 dB for 3000-6000MHz						
VSWR	≤1.20 for DC-3000MHz ≤1.25 for 3000-6000MHz						
Attenuation	1-9 dB	10 dB	15 dB	20 dB	25 dB	30 dB	40 dB
Accuracy	±0.5 dB	±0.5 dB	±0.5 dB	±0.6 dB	±0.8 dB	±0.8 dB	±1.0 dB
Power Handling	1 watt						
Impedance	50 ohms						

### Material Specifications

Cavity	Cavity Enclosure	Aluminum alloy
	Cavity Outer Surface Treatment	Conductive oxidation
	Cavity Inner Surface Treatment	Cu3Ag1
	Inner Conductor	Aluminum alloy
Connector	Inner Conductor Surface Treatment	Ag1
	Outer Conductor	Brass
	Outer Conductor Surface Treatment	Tri-metal CuSnZn3
	Inner Conductor	Brass
	Inner Conductor Surface Treatment	Ag1
	Insulator	PTFE/TPX
	Gasket	Silicon rubber

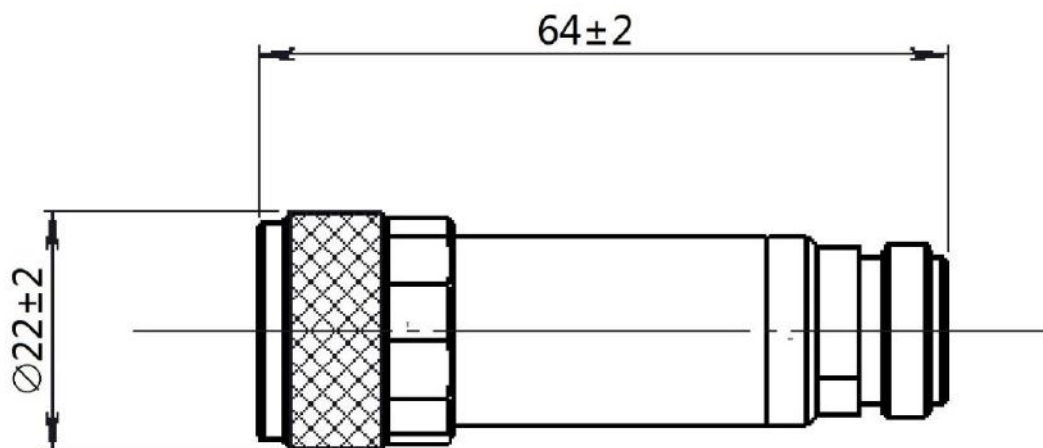
## Mechanical Specifications

Dimension	φ22×64 mm (Excluding connectors and brackets)
Weight	80 g
Connectors Type	N male to N female
Mounting	Plane
Packing	1pcs in box

## Environmental Specifications

Operating Temperature	-40 °C to +65 °C
Storage Temperature	-45 °C to +85 °C
Relative Humidity	5% - 95%
Application	Indoor

## Outline Drawing



## Regulatory Compliances

ISO 9001:2015	Compliant
ROHS	Compliant
China RoHS	Compliant
UK RoHS	Compliant
REACH	Compliant
EU/CE	Compliant

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